

Abstracts

High Power GaAs IMPATT Amplifiers (1977 [MWSYM])

K. Nishitani, H. Sawano, T. Ishii, S. Mitsui, E. Kaji and A. Amano. "High Power GaAs IMPATT Amplifiers (1977 [MWSYM])." 1977 MTT-S International Microwave Symposium Digest 77.1 (1977 [MWSYM]): 231-233.

10 Watts P-N junction GaAs IMPATT diodes with MTTF more than 10^6 hours have been developed. Using these diodes, amplifiers of 5 Watts output power, 10-dB gain, 17 per cent efficiency, 150 MHz bandwidth and 80-dB thermal noise (S/N) have been constructed.

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